



PATENT
Customer No. 22,852
Attorney Docket No. 04329.2210

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Katsuhiko HIEDA et al.

Serial No.: 09/469,190

Filed: December 21, 1999

For: SEMICONDUCTOR DEVICE AND
METHOD FOR MANUFACTURING
THE SAME

) Group Art Unit: 2811

) Examiner: H. Vu

#9
Pre
Amendment
JONES
RECEIVED
6-27-01

TECHNOLOGY CENTER 2800
JUN 26 2001

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above application, please amend this application
as follows:

IN THE CLAIMS:

Please amend claim 18 and add new claim 24, as follows:

18. (Amended) A semiconductor device according to claim 16, wherein the
capacitor insulating film is one selected from the group consisting of SrTiO_3 , $(\text{Ba},$
 $\text{Sr})\text{TiO}_3$, Ta_2O_5 , and $\text{Pb}(\text{Zr}, \text{Ti})\text{O}_3$.

Please add new claim 24, as follows:

--24. A semiconductor device according to claim 10, wherein the lower
electrode is used as a memory cell of a stack-type DRAM.--

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